Corrigendum-influence of excitation power on temperature-dependent photoluminescence of phase-separated InGaN quantum wells

Haiyan Lü (吕海燕)[1], Yuanjie Lü (吕元杰)[2], Qiang Wang (王 强)[1], Jianfei Li (李建飞)[1], Zhihong Feng (冯志红)[2], Xiangang Xu (徐现刚)[3], and Ziwu Ji (冀子武)[1,*]

[1]School of Physics, Shandong University, Jinan 250100, China
[2]National Key Laboratory of Application Specific Integrated Circuit (ASIC), Hebei Semiconductor Research Institute, Shijiazhuang 050051, China
[3]Key Laboratory of Functional Crystal Materials and Device (Ministry of Education), Shandong University, Jinan 250100, China
**Corresponding author: jiziwu@sdu.edu.cn*

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